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(54) Title: ENHANCED STATE DUAL MEMORY CELL

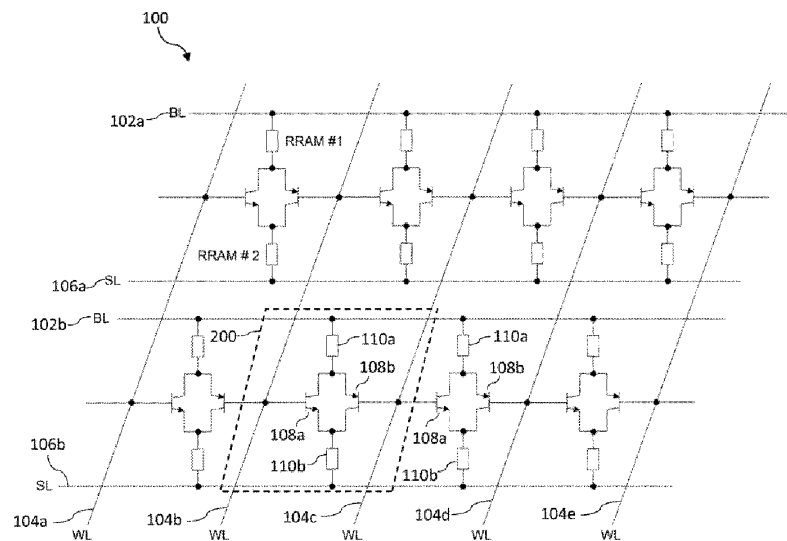


FIG. 1

(57) Abstract: A circuit includes a memory cell. The memory cell includes a first memory element, a second memory element, a first transistor, and a second transistor. The first memory element is connected to a bit line. The second memory element is connected to a select line. The first transistor is connected to a first word line. The second transistor is connected to a second word line. The first memory element is programmed by applying a first write voltage to the bit line, applying a second write voltage to the second word line, applying a first intermediate voltage to the select line, and applying a second intermediate voltage to the first word line. The select line is connected to a high impedance. The first write voltage may be a positive supply voltage, the second write voltage may be a negative supply voltage.

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